BGU7032 1 GHz wideband low-noise amplifier with bypass

Rev. 2 — 14 September 2010

Product data sheet

Product profile 1.

1.1 General description

The BGU7032 MMIC is a wideband amplifier with bypass mode. It is designed specifically for high linearity, low-noise applications over a frequency range of 40 MHz to 1 GHz. It is especially suited to Set-Top Box applications.

The LNA is housed in a 6-pin SOT363 plastic SMD package.

CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Therefore care should be taken during transport and handling.

1.2 Features and benefits

- Internally biased
- Programmable between G_p = 10 dB and bypass
- Flat gain between 40 MHz and 1 GHz
- Noise figure of 4.5 dB
- High linearity with an IP3_O of 29 dBm
- 75 Ω input and output impedance
- Power-down during bypass mode
- Bypass mode current consumption < 5 mA</p>
- ESD protection > 2 kV Human Body Model (HBM) on all pins

1.3 Applications

- Terrestrial and cable Set-Top Boxes (STB)
- Silicon and "Can" tuners
- Personal and Digital Video Recorders (PVR and DVR)
- Home networking and in-house signal distribution



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1.4 Quick reference data

Table 1. Quick reference data

 $T_{amb} = 25 \ ^{\circ}C$; typical values at $V_{CC} = 5 \ V$; $Z_S = Z_L = 75 \ \Omega$; $R_{bias} = 43 \ \Omega$; 40 MHz $\leq f_1 \leq 1000 \ MHz$.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{CC}	supply voltage	RF input AC coupled		4.75	5.0	5.25	V
I _{CC(tot)}	total supply current	G _p = 10 dB mode	[1]	-	43	-	mA
		bypass mode	[1]	-	4	-	mA
T _{amb}	ambient temperature			-10	-	+70	°C
NF	noise figure	G _p = 10 dB mode	[1]	-	4.5	-	dB
		bypass mode	[1]	-	2.5	-	dB
P _{L(1dB)}	output power at 1 dB gain compression	1 GHz; G _p = 10 dB mode	<u>[1]</u>	-	14	-	dBm
IP3 ₀	output third-order intercept point	G _p = 10 dB mode	[1][2]	-	29	-	dBm

[1] Mode depends on setting of V_{CTRL} ; see <u>Table 8</u>.

[2] The fundamental frequency (f₁) is 1000 MHz. The intermodulation product (IM3) is $2 \times f_2 - f_1$, where $f_2 = f_1 \pm 1$ MHz. Input power $P_i = -10$ dBm.

2. Pinning information

Table 2.	Pinning		
Pin	Description	Simplified outline	Graphic symbol
1	RF_OUT		
2	V _{CC}		\mathbf{N}^{3}
3	n.c.		6-1
4	CTRL		
5	GND	1 2 3	5 4 sym141
6	RF_IN		-j

3. Ordering information

Table 3. Ordering information							
Type number Package							
	Name	Description	Version				
BGU7032	-	plastic surface-mounted package; 6 leads	SOT363				

4. Marking

Table 4. Marking codes		
Type number	Marking code	
BGU7032	SD%	

Note: % character indicates the location of production.

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5. Limiting values

Table 5.Limiting valuesIn accordance with the Absolute Maximum Rating System (IEC 60134).							
Symbol	Parameter	Conditions		Min	Max	Unit	
V _{CC}	supply voltage	RF input AC coupled		-0.6	5.25	V	
V _{ctrl(Gp)}	power gain control voltage	pin CTRL	<u>[1]</u>	0	V_{CC}	V	
I _{CC(tot)}	total supply current			-	60	mA	
P _{tot}	total power dissipation	$T_{sp} \le 100 \ ^{\circ}C$	[2]	-	250	mW	
Pi	input power	single tone		-	10	dBm	
T _{stg}	storage temperature			-65	+150	°C	
Tj	junction temperature			-	150	°C	
T _{amb}	ambient temperature			-10	+70	°C	
V _{ESD}	electrostatic discharge voltage	Human Body Model (HBM); according to JEDEC standard 22-A114E		2	-	kV	

[1] $V_{ctrl(Gp)}$ must not exceed V_{CC}; I_{CTRL} must be limited to 5 mA (maximum).

[2] T_{sp} is the temperature at the solder point of the ground lead.

Remark: V_{ctrl(Gp)} must not exceed V_{CC}; I_{CTRL} must be limited to a maximum of 5 mA.

6. Thermal characteristics

Table 6.	Thermal characteristics			
Symbol	Parameter	Conditions	Тур	Unit
R _{th(j-sp)}	thermal resistance from junction to solder point		240	K/W

7. Characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{CC}	supply voltage	RF input AC coupled		4.75	5.0	5.25	V
I _{CC(tot)}	total supply current	G _p = 10 dB mode	[1]	-	43	-	mA
	bypass mode	[1]	-	4	-	mA	
$ s_{21} ^2$	insertion power gain	G _p = 10 dB mode	[1]	-	10	-	dB
	bypass mode	[1]	-	-2	-	dB	
SL _{sl}	slope straight line			-	-1	-	dB
FL	flatness of frequency response			-	-0.2	-	dB
NF	noise figure	G _p = 10 dB mode	[1]	-	4.5	-	dB
		bypass mode	[1]	-	2.5	-	dB
RL _{in}	input return loss	G _p = 10 dB mode	[1]	-	18	-	dB
		bypass mode	[1]	-	8	-	dB

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Table 7. Characteristics continued	Table 7.	Characteristics	continued
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 $T_{amb} = 25 \ ^{\circ}C$; typical values at $V_{CC} = 5 \ V$; $Z_S = Z_L = 75 \ \Omega$; $R_{bias} = 43 \ \Omega$; 40 MHz $\leq f_1 \leq 1000 \ MHz$.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
RL _{out}	output return loss	G _p = 10 dB mode	<u>[1]</u>	-	12	-	dB
		bypass mode	<u>[1]</u>	-	8	-	dB
P _{L(1dB)}	output power at 1 dB gain compression	1 GHz; G _p = 10 dB mode	[1]	-	14	-	dBm
IP3 ₀	output third-order intercept point	G _p = 10 dB mode	[1][2]	-	29	-	dBm
		bypass mode	[1][2]	-	29	-	dBm

[1] Mode depends on setting of V_{ctrl(Gp)} (V_{CTRL}); see <u>Table 8</u>.

[2] The fundamental frequency (f₁) is 1000 MHz. The intermodulation product (IM3) is $2 \times f_2 - f_1$, where $f_2 = f_1 \pm 1$ MHz. Input power $P_i = -10$ dBm.

Table 8. Gain selection (pin CTRL)

-10 °C \leq T_{amb} \leq +70 °C; recommended power-up condition: V_{CTRL} = logic 0 or < 0.7 V.

V _{ctrl(Gp)} (V _{CTRL}) (V)	Mode
≤ 0.7	bypass
≥ 4.3	$G_p = 10 \text{ dB}$

Remark: V_{ctrl(Gp)} must not exceed V_{CC}; I_{CTRL} must be limited to a maximum of 5 mA.

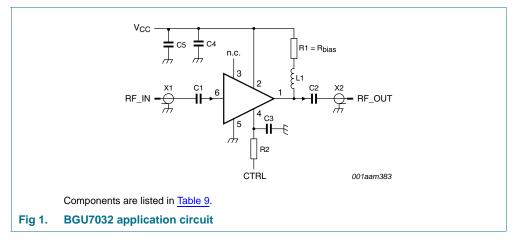
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Application information 8.

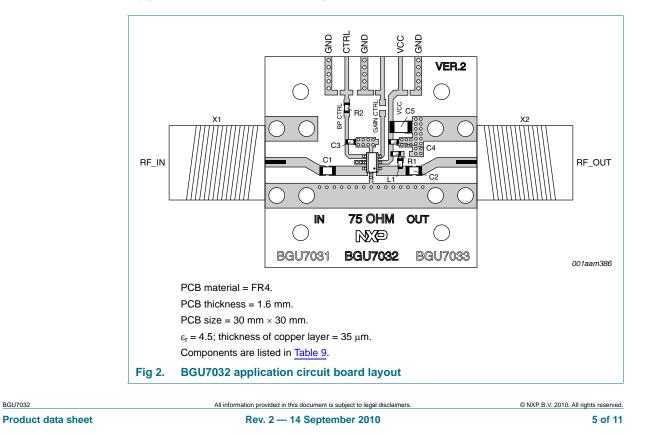
Other applications are possible. Please contact your local sales representative for more information. Application notes are available on the NXP website.

8.1 **Application circuit**



All control and supply lines must be decoupled properly. The decoupling capacitors must be placed as close to the device as possible.

8.2 Application circuit board layout



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Table 9.List of componentsSee Figure 1 and Figure 2

See <u>Figure 1</u> and <u>Figure 2</u> .								
Component	Description	Value		Remarks	Function			
C1, C2	capacitor	10 nF			DC blocking			
C3, C4	capacitor	10 nF			decoupling			
C5	capacitor	10 μF			decoupling			
L1	chip ferrite bead	$1.5 \ \text{k}\Omega$	[1]	Murata BLM18HE152SN1DF	RF choke			
R1	resistor	43 Ω	[1]	R _{bias}	bias setting			
R2	resistor	1.8 kΩ			current limiting			
X1, X2	connector	75 Ω		F-connector, edge mount PCB reflow type, Bomar 861V509ERG	input/output			

[1] L1 and R1 must have a power rating of 0.1 W or higher.

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9. Package outline

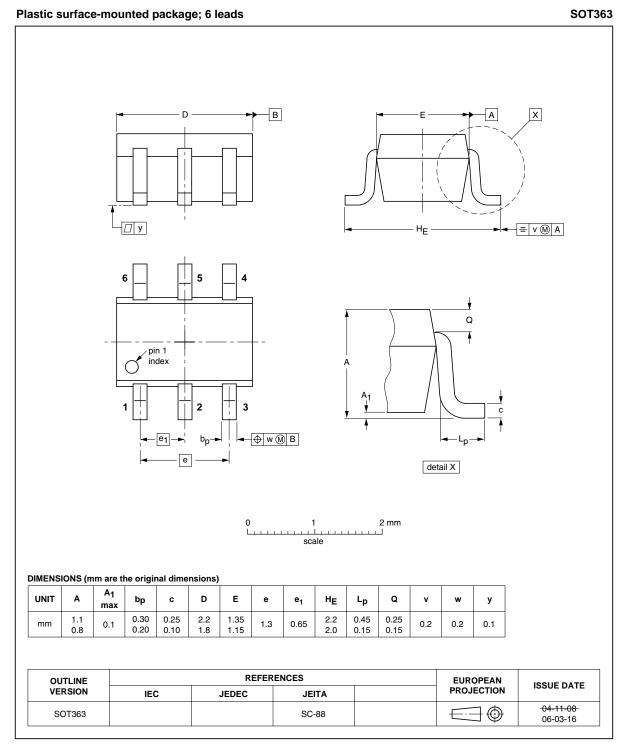


Fig 3. Package outline SOT363

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10. Abbreviations

Table 10. Abbreviations		
Acronym	Description	
AC	Alternating Current	
DC	Direct Current	
LNA	Low-Noise Amplifier	
MMIC	Monolithic Microwave Integrated Circuit	
PCB	Printed-Circuit Board	
RF	Radio Frequency	
SMD	Surface-Mounted Device	

11. Revision history

Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BGU7032 v.2	20100914	Product data sheet	-	BGU7032 v.1
Modifications:	 The status of 	of this data sheet has been ch	anged to Product data	a sheet.
BGU7032 v.1	20100817	Preliminary data sheet	-	-

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12. Legal information

12.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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[2] The term 'short data sheet' is explained in section "Definitions".

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